TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L62AE

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

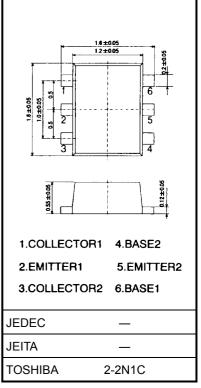
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rat	Unit	
Characteristics		Q1	Q2	Offic
Collector-base voltage	V _{CBO}	10	10	V
Collector-emitter voltage	V _{CEO}	5	5	V
Emitter-base voltage	V _{EBO}	1.5	2	V
Collector current	IC	25	40	mA
Base current	ΙΒ	10	10	mA
Collector power dissipation	P _C (Note1)	100		mW
Junction temperature	Tj	125		°C
Storage temperature range	T _{stg}	-55~125		°C

Note1: Total power dissipation of Q1 and Q2

	Q1	Q2
Three pin SSM type part No.	MT3S07S	MT3S03AS

Unit: mm



Weight: 3 mg (typ.)

Electrical Characteristics Q1-Side (Ta = 25°C)

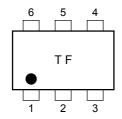
Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$		_	0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V}, I_{C} = 0$		_	1	μΑ
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V, } I_{C} = 5 \text{ mA}$	70	_	140	_
Transition frequency	f _T	$V_{CE} = 3 \text{ V, } I_{C} = 10 \text{ mA}$	10	12	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	7	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 15 \text{ mA}, f = 2 \text{ GHz}$	6.5	8.5	_	ub l
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.6	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.5	3	UB
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note2)	_	0.45	0.85	pF

Electrical Characteristics Q2-Side (Ta = 25°C)

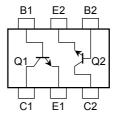
Characteristics	Symbol	Test Condition		Тур.	Max	Unit	
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$		_	0.1	μΑ	
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V, } I_{C} = 0$		_	1	μА	
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V, } I_{C} = 5 \text{ mA}$	80	_	160	_	
Transition frequency	f _T (1)	$V_{CE} = 1 \text{ V, } I_{C} = 5 \text{ mA}$	5	7	_	GHz	
	f _T (2)	V _{CE} = 3 V, I _C = 10 mA	7	10	_	GHZ	
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	_	5	_	dB	
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	3	6.5	_	ub	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB	
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	_	1.4	2.2		
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note2)	_	0.8	1.15	pF	

Note2: C_{re} is measured by 3 terminal method with capacitance bridge.

Marking



Pin Assignment (top view)



Caution

This device electrostatic sensitivity. Please handle with caution.

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